

www.vishay.com

Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 16 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V						
V <sub>TM</sub>	1.25 V						
I <sub>GT</sub>	45 mA						
T <sub>J</sub>	-40 °C to 125 °C						
Package	TO-220AB 3L						
Circuit configuration	Single SCR						

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	18	22	А					

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	16	A						
I <sub>RMS</sub>		25	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		800, 1200	V						
I <sub>TSM</sub>		320	Α						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/μs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-25TTS08-M3	800	800	10						
VS-25TTS12-M3	1200	1200	10						

# VS-25TTS08-M3, VS-25TTS12-M3

# Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS								
DADAMETED	SYMBOL	TEST 001	NDITIONS	VAL	UNITS			
PARAMETER	SYMBOL TEST CONDITIONS		TYP.	MAX.	JUNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduc	tion half sine wave	16				
Maximum RMS on-state current	I <sub>RMS</sub>			2	25	Α		
Maximum peak, one-cycle,	1	10 ms sine pulse, rated \	/ <sub>RRM</sub> applied	2	70	_ A		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volt	age reapplied	3	20			
Marriage up 12t for fraing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied			365			
Maximum I <sup>2</sup> t for fusing	I-I	10 ms sine pulse, no volt	515		– A <sup>2</sup> s			
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no volta	5152		A²√s			
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.25		٧		
On-state slope resistance	r <sub>t</sub>	T <sub>J</sub> = 125 °C		12.0		mΩ		
Threshold voltage	V <sub>T(TO)</sub>	1J = 125 C		1.0		V		
Maximum reverse and direct leakage current	1/1	T <sub>J</sub> = 25 °C	V <sub>B</sub> = Rated V <sub>BBM</sub> /V <sub>DBM</sub>	0	.5			
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C	VR = hated VRRM/VDRM	10				
Holding current	l <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		ı	150	mA		
Maximum latching current	lμ	Anode supply = 6 V, resi	200					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80$	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g ^{-}\text{k} = \text{Open}$					
Maximum rate of rise of turned-on current	dl/dt			1:	A/µs			

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60		
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	.,	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.25		
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA	

SWITCHING									
PARAMETER SYMBOL TEST CONDITIONS VALUES									
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9						
Typical reverse recovery time t <sub>rr</sub>		T <sub>J</sub> = 125 °C	4	μs					
Typical turn-off time	t <sub>q</sub>	1J = 125	110						

### www.vishay.com

## Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.1				
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W			
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5				
Approximate weight				2	g			
Approximate weight				0.07	oz.			
Mounting torque -	minimum			6 (5)	kgf · cm			
wounting torque –	maximum			12 (10)	(lbf · in)			
Marking dayion			Consectula TO 220AP 21	25TTS08				
Marking device		Case style TO-220AB 3L		25TTS12				

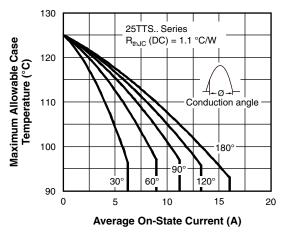


Fig. 1 - Current Rating Characteristics

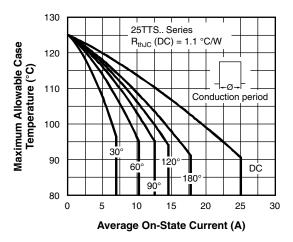


Fig. 2 - Current Rating Characteristics

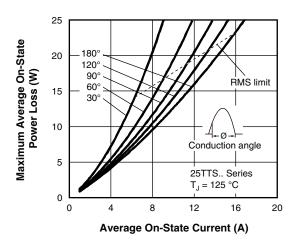


Fig. 3 - On-State Power Loss Characteristics

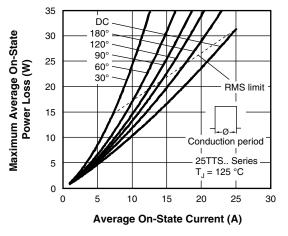


Fig. 4 - On-State Power Loss Characteristics

### Vishay Semiconductors

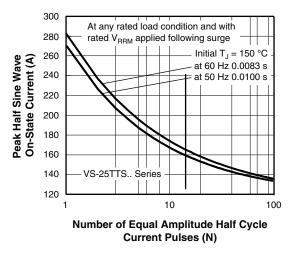


Fig. 5 - Maximum Non-Repetitive Surge Current

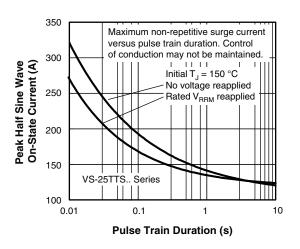


Fig. 6 - Maximum Non-Repetitive Surge Current

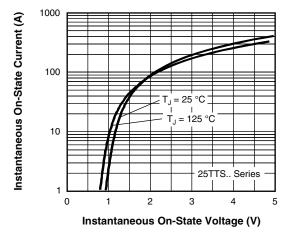


Fig. 7 - On-State Voltage Drop Characteristics

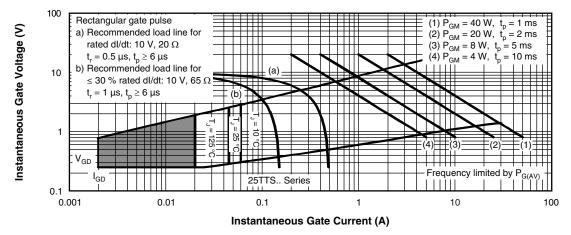


Fig. 8 - Gate Characteristics

### Vishay Semiconductors

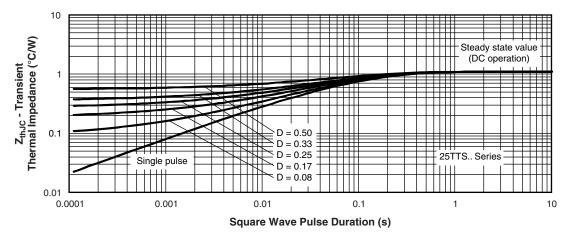
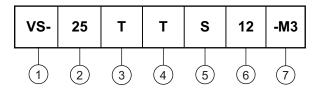


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

- Current rating (25 = 25 A)

- Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating -- 08 = 800 V 12 = 1200 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS08-M3	50	Antistatic plastic tubes					
VS-25TTS12-M3	50	Antistatic plastic tubes					

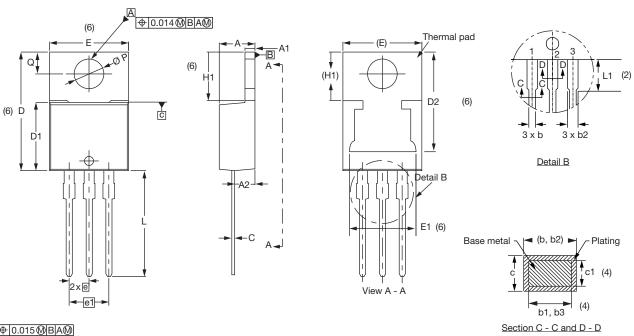
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96154</u>						
Part marking information	www.vishay.com/doc?95028					



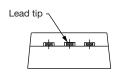
### Vishay Semiconductors

### **3L TO-220AB**

#### **DIMENSIONS** in millimeters and inches



#### **⊕** 0.015 **M** B A **M**



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355		1		•			•	

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.